

Notice of References Cited	Application/Control Number 10/047,323	Applicant(s)/Patent Under Reexamination LAMPERT ET AL.
	Examiner Matthew J Song	Art Unit 1765

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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-5,354,384	10-1994	Sneed et al.	134/6
	B	US-3,675,619	07-1972	Burd, John W.	118/719
	C	US-5,861,346	01-1999	Hamza et al.	438/769
	D	US-6,110,279	08-2000	Kito et al.	117/105
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	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N	JP 62091492 A	04-1987	Japan	TASHIRO, YOSHIHARU	C30B 23/08
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Kaneda et al. "MBE Growth of 3C SiC/ 6H SiC and the Electric Properties of Its p-n Junction", Journal of Crystal Growth 81(1987) pg 536-542.
	V	Patent Abstracts of Japan. English Abstract of JP 62-091492 (1987).
	W	
	X	

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.